Number	Hit	Search Text	DB	Time stamp
245	21	(pad sam (parasiti n ar5 (s r or r tifier))	USPAT;	2004/06/08
		and ((rectifi r or scr) near10 (I w near	US-PGPUB;	16:07
		v Itag)))	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
246	0	(pad same (parasitic near5 (scr or rectifier))	USPAT;	2004/06/08
		and ((rectifier or scr) near10 (low near	US-PGPUB;	16:07
		voltage))).clm.	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
247	3	(pad same (parasitic near5 (scr or rectifier))	USPAT;	2004/06/08
		and ((rectifier or scr) near10 (low near	US-PGPUB;	16:08
		voltage))).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
248	5	(pad near10 (parasitic near5 (scr or	USPAT;	2004/06/08
		rectifier)) and ((rectifier or scr) near10 (low	US-PGPUB;	16:09
		near voltage)))	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
249	2	(pad near10 (parasitic near5 (scr or	USPAT;	2004/06/08
		rectifier)) and ((rectifier or scr) near10 (low	US-PGPUB;	16:09
		near voltage))) and pad.clm.	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
250	2	(pad near10 (parasitic near5 (scr or	USPAT;	2004/06/08
		rectifier)) and ((rectifier or scr) near10 (low	US-PGPUB;	16:09
		near voltage))) and pad.clm. and diode	EPO; JPO;	
			DERWENT;	
054	_		IBM_TDB	
251	0	(pad near10 (parasitic near5 (scr or	USPAT;	2004/06/08
		rectifier)) and ((rectifier or scr) near10 (low	US-PGPUB;	16:09
		near voltage))) and pad.clm. and diode.clm.	EPO; JPO;	
			DERWENT;	
050	450		IBM_TDB	
252	158	diode.clm. and (mosfet or mos or	USPAT;	2004/06/08
		transistor).clm. and pad.clm. and esd.clm.	US-PGPUB;	16:09
			EPO; JPO;	
			DERWENT;	
252	20	diada da almanad (m	IBM_TDB	0004/00/00
253	32	diode.clm. and (mosfet or mos or	USPAT;	2004/06/08
		transistor).clm. and pad.clm. and esd.clm.	US-PGPUB;	16:10
		and (scr or rectifier).clm.	EPO; JPO;	
			DERWENT;	
254	_	did les and 6 8 4	IBM_TDB	0004/00/07
254	4	did. Im. and (m sf t rmos r	USPAT;	2004/06/08
		transistor). Im. and pad. Im. and sd.clm.	US-P PUB;	16:10
		•	•	33333
		and (s rorr tifi r).clm. and (I w near v Itag).clm.	EPO; JPO; DERWENT;	

255	1	diode.clm. and (m sf t r mos or	USPAT;	2004/06/08
		transist r). lm. and pad.clm. and esd.clm.	US-P PUB;	16:18
		and (s r rrectifi r).clm. and (I w n ar	EPO; JPO;	
		v Itage).clm. and (pad n ar10 di de near10	DERWENT;	
		(mos or mosfet or transistor)). Im.	IBM_TDB	
256	94	(di de near10 (transistor r m sf t or m s)	USPAT;	2004/06/08
		near10 pad).clm.	US-PGPUB;	16:19
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
257	5	(diode near10 (transistor or mosfet or mos)	USPAT;	2004/06/08
		near10 pad).clm. and (scr or rectifier).clm.	US-PGPUB;	16:20
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
258	3	(diode near10 (transistor or mosfet or mos)	USPAT;	2004/06/08
		near10 pad).clm. and (scr or rectifier).clm.	US-PGPUB;	16:20
		and ((rectifier or scr) near10 esd)	EPO; JPO;	
		((,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	DERWENT;	
			IBM_TDB	
259	1	(diode near10 (transistor or mosfet or mos)	USPAT;	2004/06/08
	1	near10 pad).clm. and (scr or rectifier).clm.	US-PGPUB;	16:22
		and ((rectifier or scr) near10 (esd near	EPO; JPO;	
		current))	DERWENT;	
			IBM_TDB	
260	1	(diode near10 (transistor or mosfet or mos)	USPAT;	2004/06/08
	_	near10 pad).clm. and (scr or rectifier).clm.	US-PGPUB;	16:22
		and ((rectifier or scr or lyscr) near10 (esd	EPO; JPO;	
		near current))	DERWENT;	
		,,	IBM_TDB	
261	116	((rectifier or scr or lyscr) near10 (esd near	USPAT;	2004/06/08
		current))	US-PGPUB;	16:22
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
262	2	((rectifier or scr or lvscr) near10 (esd near	USPAT;	2004/06/08
		current)).clm.	US-PGPUB;	16:23
		,	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
263	2	((rectifier or scr or lvscr) near10 (esd near	USPAT;	2004/06/08
		current) near10 (lvscr or (low near	US-PGPUB;	16:24
		voltage)))	EPO; JPO;	
		5 -7//	DERWENT;	
			IBM_TDB	
264	730	((rectifier or scr or lvscr) near10 (current)	USPAT;	2004/06/08
		near10 (lvscr or (low near voltage)))	US-PGPUB;	16:24
		(EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	·	l		L

265	44	/ -	HCDAT.	2004/00/09
265	14	(sd near10 (rectifi r or scr or lyscr) near10	USPAT;	2004/06/08
		(urr nt) n ar10 (lvscr or (l w near	US-PGPUB;	16:25
		v Itage)))	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
266	1	(esd n ar10 (rectifier r cr r lvscr) n ar10	USPAT;	2004/06/08
		(current) near10 (lvscr or (low near	US-PGPUB;	16:26
		voltage)) near10 (distribute or distributing	EPO; JPO;	
		or distributed or distribution or pass or	DERWENT;	
		passed))	IBM_TDB	
267	5	((Ivscr or (Iow near current)) near10 diode	USPAT;	2004/06/08
		near10 esd)	US-PGPUB;	16:27
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
268	0	((Ivscr)).clm.	USPAT;	2004/06/08
			US-PGPUB;	16:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
269	14	((Ivscr))	USPAT;	2004/06/08
			US-PGPUB;	16:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
270	0	((Ivscr)) and pad.clm. and diode.clm.	USPAT;	2004/06/08
			US-PGPUB;	16:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
271	11	((Ivscr)) and pad and diode	USPAT;	2004/06/08
		·	US-PGPUB;	16:29
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
272	2	((Ivscr)) and (pad same diode same	USPAT;	2004/06/08
		(transistor or mosfet or mos))	US-PGPUB;	16:30
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
273	2	(diode near10 (transistor or mosfet or mos)	USPAT;	2004/06/08
		near10 pad near10 (rectifier or scr or	US-PGPUB;	16:34
		Isvscr) near10 esd)	EPO; JPO;	,
			DERWENT;	
			IBM_TDB	
274	0	(diode near10 (transistor or mosfet or mos)	USPAT;	2004/06/08
] [near10 pad near10 (rectifier or scr or	US-PGPUB;	16:34
		lsvs r) near10 sd near10 (I w n ar2	EPO; JPO;	
		voltage))	DERWENT;	
]			IBM_TDB	

275	0	(diode n ar10 (transist r or m sf t or m s)	USPAT;	2004/06/08
		n ar10 pad near10 (rectifi r or scr or lvscr)	US-P PUB;	16:35
		near10 esd near10 (I w near2 voltage))	EPO; JP ;	
			DERWENT;	
			IBM_TDB	
276	2	((diode near10 (transistor or m sfet or mos)	USPAT;	2004/06/08
		near10 pad near10 (rectifier or scr or lvscr)	US-PGPUB;	16:38
		near10 esd) same (low near2 voltage))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
277	13	((diode near10 (transistor or mosfet or mos)	USPAT;	2004/06/08
		near10 (rectifier or scr or lvscr) near10 esd)	US-PGPUB;	16:38
		same (low near2 voltage))	EPO; JPO;	
		• "	DERWENT;	
			IBM_TDB	
278	2	((diode near10 (transistor or mosfet or mos)	USPAT;	2004/06/08
		near10 (rectifier or scr or lyscr) near10 esd)	US-PGPUB;	16:38
		same (low near2 voltage) same (esd near	EPO; JPO;	
		current))	DERWENT;	
		<i>"</i>	IBM_TDB	
279	3	((diode near10 (transistor or mosfet or mos)	USPAT;	2004/06/08
		near10 (rectifier or scr or lyscr)) same (low	US-PGPUB;	16:41
		near2 voltage) same (esd near current))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
280	6	((diode near20 (transistor or mosfet or mos)	USPAT;	2004/06/08
		near20 (rectifier or scr or lvscr)) same (low	US-PGPUB;	16:42
		near2 voltage) same (esd near current))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
281	31	((rectifier or scr or lvscr) near10 (low near2	USPAT;	2004/06/08
		voltage) same (esd near current))	US-PGPUB;	16:42
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
282	5	((rectifier or scr or lvscr) near10 (low near2	USPAT;	2004/06/08
		voltage) near10 (esd near current))	US-PGPUB;	16:44
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
283	7	((rectifier or scr or lvscr) near20 (low near2	USPAT;	2004/06/08
		voltage) near20 (esd near current))	US-PGPUB;	16:44
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
284	1190	((rectifier or scr or lvscr) near20 (low near2	USPAT;	2004/06/08
		voltage) near20 (current))	US-PGPUB;	16:45
			EPO; JP ;	
•	[DERWENT;	
			IBM_TDB	

285	8	((r ctifi r or scr or lvs r) n ar20 (l w n ar2	USPAT;	2004/06/08
		v Itag) near20 (current)).ti,ab, lm. and	US-PGPUB;	16:45
		esd.ti,ab,clm.	EP ; JPO;	
			DERWENT;	
			IBM_TDB	
286	3	((r tifier rscrorlvs r) near20 (I w near2	USPAT;	2004/06/08
		voltage) near20 (current)).ti,ab,clm. and	US-PGPUB;	16:45
	(esd.ti,ab,clm. and parasitic.ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
287	1	((rectifier or scr or lvscr) near20 (low near2	USPAT;	2004/06/08
		voltage) near20 (current)).ti,ab,clm. and	US-PGPUB;	16:47
		esd.ti,ab,clm. and parasitic.ti,ab,clm. and	EPO; JPO;	
		diode.clm.	DERWENT;	
200		//	IBM_TDB	0004/00/00
288	1	((rectifier or scr or lyscr) near20 (low near2	USPAT;	2004/06/08
		voltage) near20 (current)).ti,ab,clm. and	US-PGPUB;	16:47
		esd.ti,ab,clm. and parasitic.ti,ab,clm. and (diode near10 transistor).ti,ab,clm.	EPO; JPO;	
		(uloue nearlo transistor).ti,ab,cim.	DERWENT;	
289	94	(diode near10 (mos or mosfet or transistor)	IBM_TDB USPAT;	2004/06/08
203	54	near10 pad).clm.	US-PGPUB;	16:48
		near to paujicini.	EPO; JPO;	10.40
			DERWENT;	
			IBM_TDB	
290	26	(diode near10 (mos or mosfet or transistor)	USPAT;	2004/06/08
		near10 pad).clm. and esd.clm.	US-PGPUB;	16:48
		,,,	EPO; JPO;	13113
			DERWENT;	
			IBM_TDB	
291	3	(diode near10 (mos or mosfet or transistor)	USPAT;	2004/06/08
		near10 pad).clm. and esd.clm. and (rectifier	US-PGPUB;	16:50
]		or scr or lvscr).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	-
292	1	(diode near10 (mos or mosfet or transistor)	USPAT;	2004/06/08
		near10 pad).clm. and esd.clm. and (rectifier	US-PGPUB;	16:51
		or scr or lvscr).clm. and (low near	EPO; JPO;	
	1	voltage).clm.	DERWENT;	
			IBM_TDB	
293	2	(diode near10 (mos or mosfet or transistor)	USPAT;	2004/06/08
		near10 pad).clm. and esd.clm. and (rectifier	US-PGPUB;	16:52
		or scr or lyscr).clm. and (low near2	EPO; JPO;	
		voltage).clm.	DERWENT;	
004			IBM_TDB	
294	42	(low near2 voltage) near10 (esd near	USPAT;	2004/06/08
		current)	US-PGPUB;	16:53
			EPO; JPO;	
			DERWENT;	
L	<u> </u>		IBM_TDB	

295	15	((I w near2 v Itag) n ar10 (sd n ar	USPAT;	2004/06/08
		urrent)) and di d .ti,ab,clm. and (m sf t	US-PGPUB;	16:53
		r m s or transist r).ti,ab,clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
296	13	((I w near2 voltag) near10 (sd near	USPAT;	2004/06/08
		current)) and diode.ti,ab,clm. and (mosfet	US-PGPUB;	16:54
		or mos or transistor).ti,ab,clm. and	EPO; JPO;	
		parasitic	DERWENT;	
			IBM_TDB	
297	6	((low near2 voltage) near10 (esd near	USPAT;	2004/06/08
•		current)) and diode.ti,ab,clm. and (mosfet	US-PGPUB;	16:54
		or mos or transistor).ti,ab,clm. and	EPO; JPO;	
		parasitic and pad.clm.	DERWENT;	
			IBM_TDB	
298	4	((low near2 voltage) near10 (esd near	USPAT;	2004/06/08
	-	current)) and diode.ti,ab,clm. and (mosfet	US-PGPUB;	16:55
		or mos or transistor).ti,ab,clm. and	EPO; JPO;	10.00
		parasitic and pad.clm. and (rectifier or scr	DERWENT;	
		or lyscr).clm.	IBM_TDB	
299	2	((low near2 voltage) near10 (esd near	USPAT;	2004/06/08
	_	current)) and diode.ti,ab,clm. and (mosfet	US-PGPUB;	16:57
		or mos or transistor).ti,ab,clm. and	EPO; JPO;	10.07
		parasitic.clm. and pad.clm. and (rectifier or	DERWENT;	
		scr or lyscr).clm.	IBM_TDB	
300	o	((low near2 voltage) near10 (esd near	USPAT;	2004/06/08
		current)).clm. and diode.ti,ab,clm. and	US-PGPUB;	16:57
		(mosfet or mos or transistor).ti,ab,clm. and	EPO; JPO;	10.07
		parasitic.clm. and pad.clm. and (rectifier or	DERWENT;	
		scr or lyscr).clm.	IBM_TDB	
301	o	((low near2 voltage) same (esd near	USPAT;	2004/06/08
		current)).clm. and diode.ti,ab,clm. and	US-PGPUB;	16:58
		(mosfet or mos or transistor).ti,ab,clm. and	EPO; JPO;	10.30
		parasitic.clm. and pad.clm. and (rectifier or	DERWENT;	
		scr or lyscr).cim.	IBM_TDB	
302	3	(diode same (mos or mosfet or transistor)	USPAT;	2004/06/08
302		same parasitic same (rectifier or scr or		2004/06/08
		lvscr) same (esd near current) same (low	US-PGPUB;	16:59
		near2 voltage))	EPO; JPO;	
		nearz voltagejj	DERWENT;	
303	2	(diode same (mos or mosfet or transistor)	IBM_TDB USPAT;	2004/06/08
	*	same parasitic same (rectifier or scr or		
		lvscr) same (esd near current) same (low	US-PGPUB;	16:59
		near2 voltage) same pad)	EPO; JPO;	
		nearz voitage, same pau)	DERWENT;	
	<u> </u>		IBM_TDB	